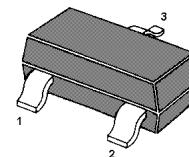
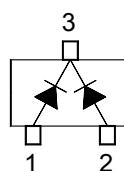


Silicon Epitaxial Planar Switching Diode

Application

- Ultra high speed switching



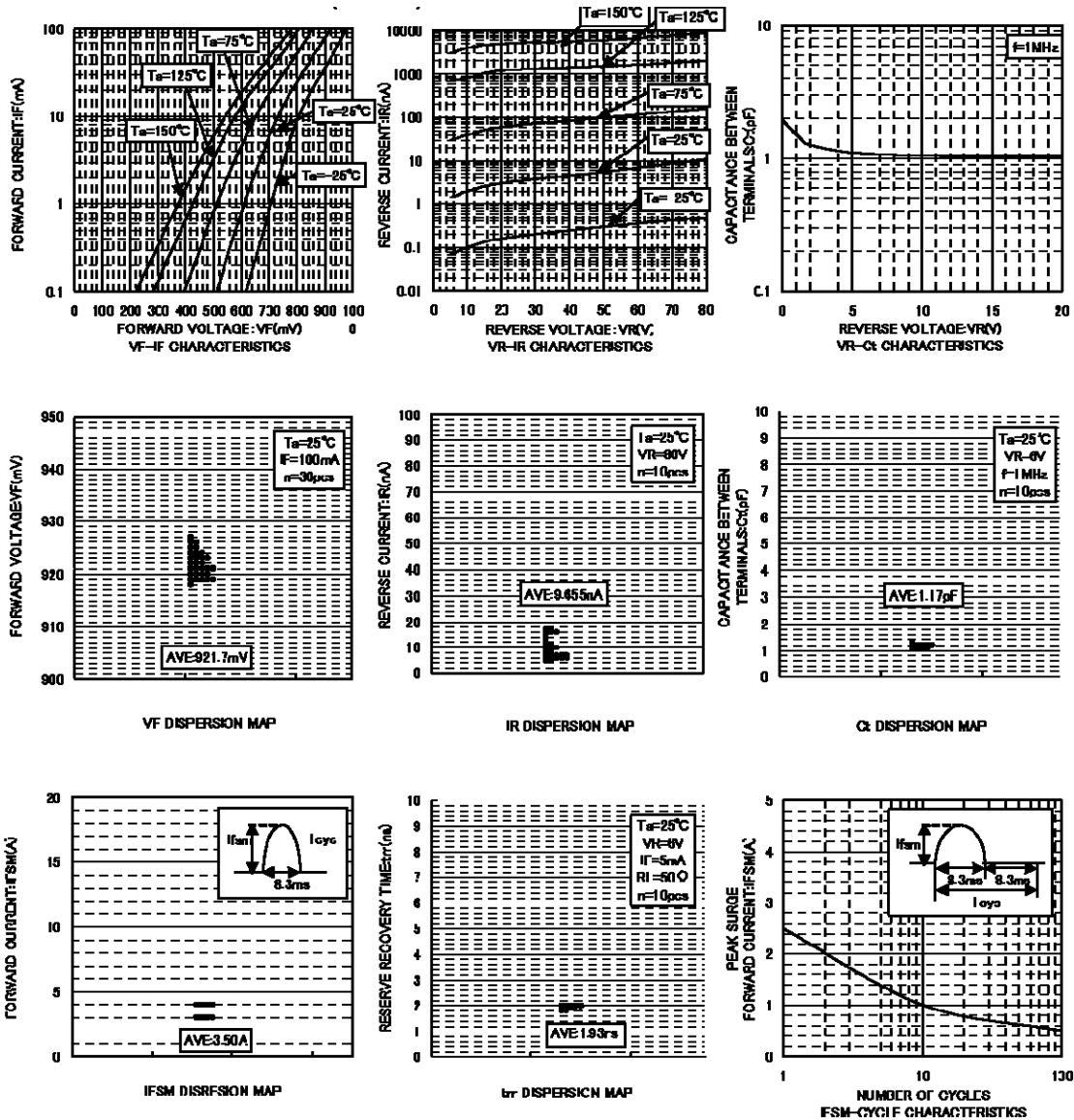
Marking Code: **A4**
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	80	V
Reverse Voltage	V_R	80	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Maximum Peak Forward Current	I_{FM}	300	mA
Non-repetitive Peak Forward Surge Current ($t = 1 \mu\text{s}$)	I_{FSM}	4	A
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at $T_a = 25^\circ\text{C}$

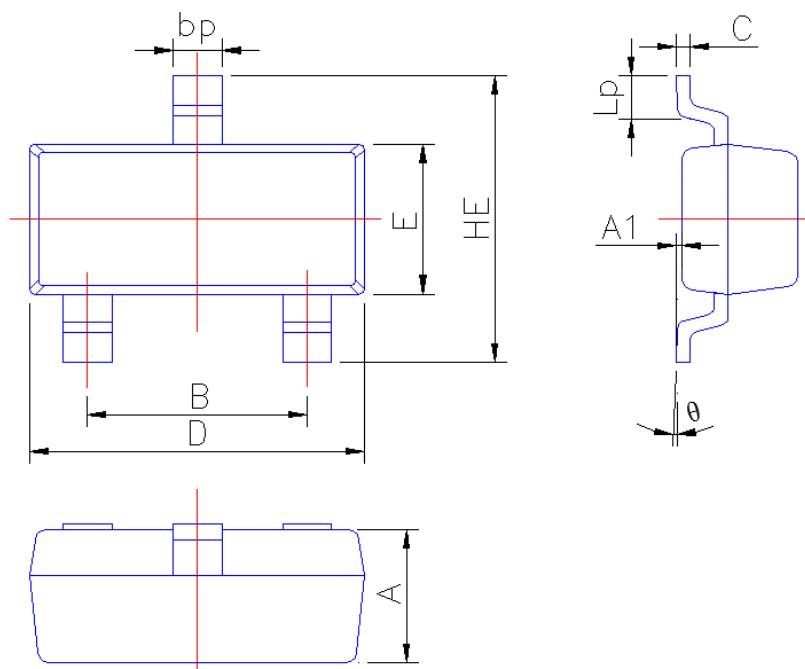
Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100 \text{ mA}$	V_F	1.2	V
Reverse Current at $V_R = 70 \text{ V}$	I_R	0.1	µA
Total Capacitance at $V_R = 6 \text{ V}, f = 1 \text{ MHz}$	C_T	3.5	pF
Reverse Recovery Time at $V_R = 6 \text{ V}, I_F = 5 \text{ mA}, R_L = 50 \Omega$	t_{rr}	4	ns



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.10
A1	0.013	0.100
B	1.80	2.00
bp	0.35	0.50
C	0.09	0.150
D	2.80	3.00
E	1.20	1.40
HE	2.20	2.80
Lp	0.20	0.50
θ	0°	5°